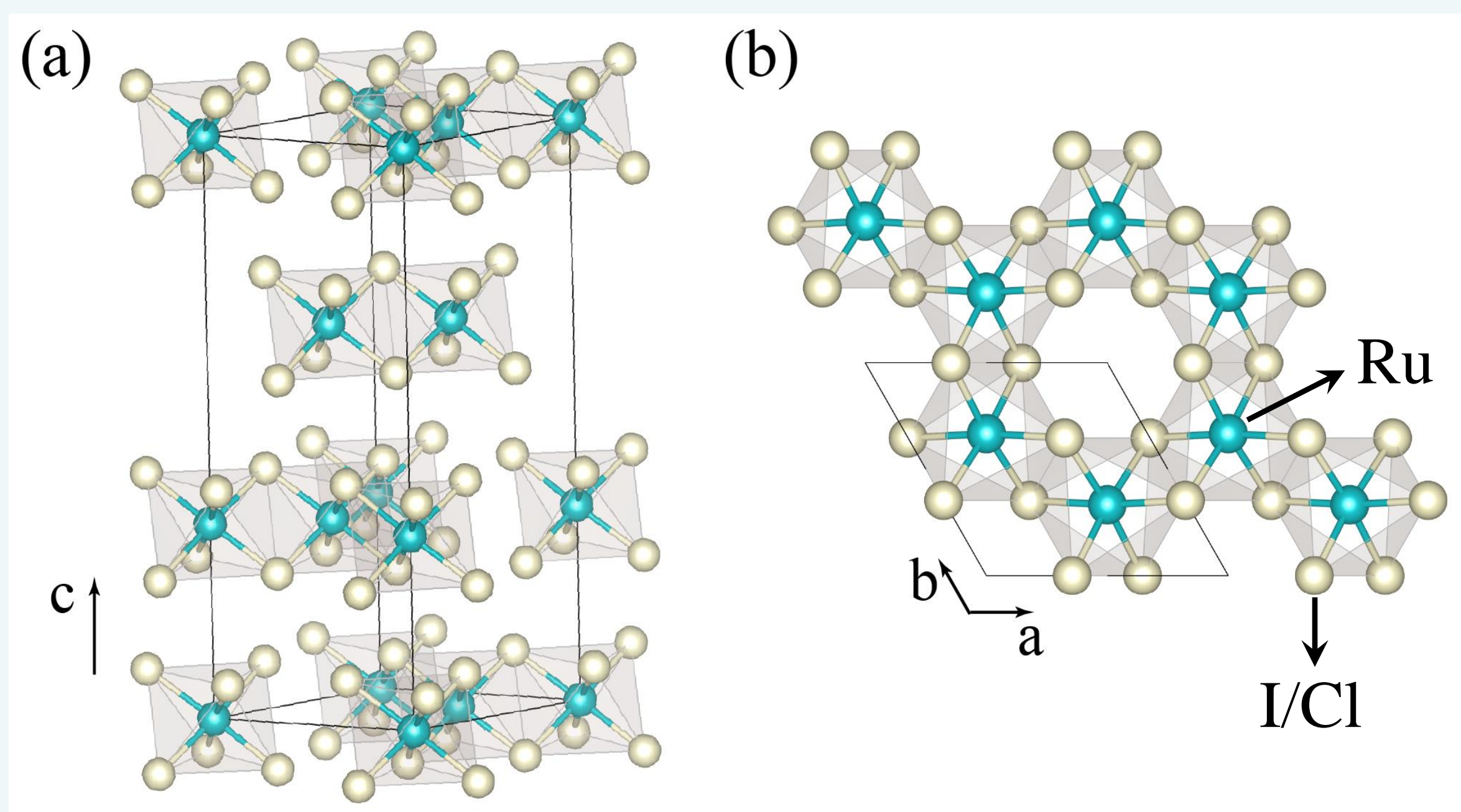




# Contrasting electronic states of $\text{RuI}_3$ and $\text{RuCl}_3$

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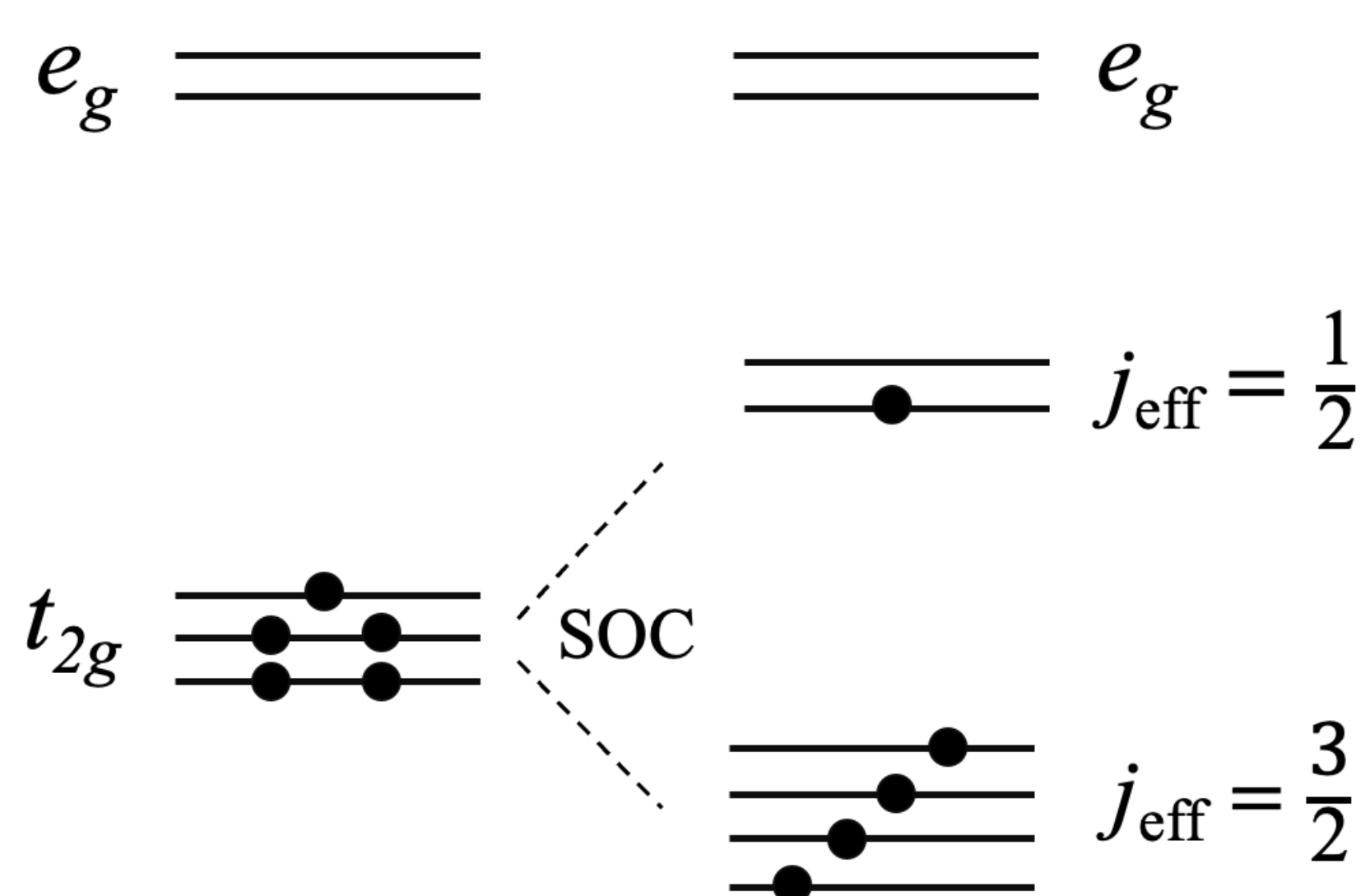


The spin-orbital entangled states are of great interest as they hold exotic phases and intriguing properties. Here we investigate the electronic and magnetic properties of  $\text{RuI}_3$  and  $\text{RuCl}_3$ . We find that the  $\text{Ru}^{3+}$  ion of  **$\text{RuI}_3$**  is in the spin-orbital entangled  $j_{\text{eff}} = 1/2$  **paramagnetic state** owing to the strong Ru 4d-I 5p hybridization, weak spin polarization, and strong SOC. More interestingly, a metal-insulator transition occurs from  $\text{RuI}_3$  bulk to monolayer. In contrast,  **$\text{RuCl}_3$**  bulk and monolayer both show Mott-insulating behavior, the  $\text{Ru}^{3+}$  ion is in the  $S = 1/2$  and  $L_x = 1$  **zigzag AFM state** due to considerable Hund exchange and trigonal crystal field splitting. This result well explains the experimental electronic and magnetic behavior of bulk  $\text{RuCl}_3$ . The present work demonstrates the contrasting spin-orbital states and the varying properties of  $\text{RuI}_3$  and  $\text{RuCl}_3$ .

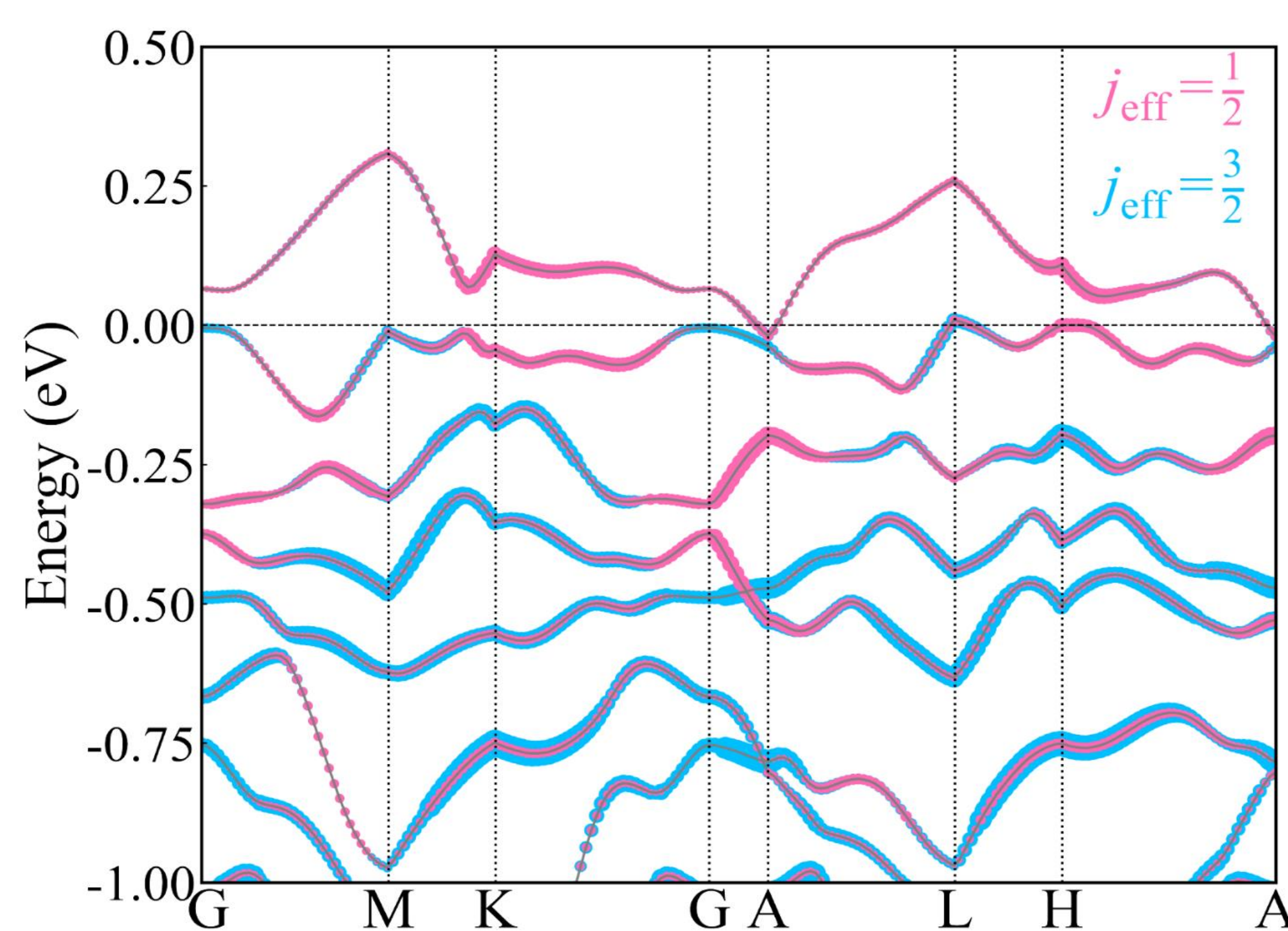
## $\text{RuI}_3$

strong Ru 4d-I 5p hybridization & weak spin polarization  $\rightarrow$  **SOC-dominant**

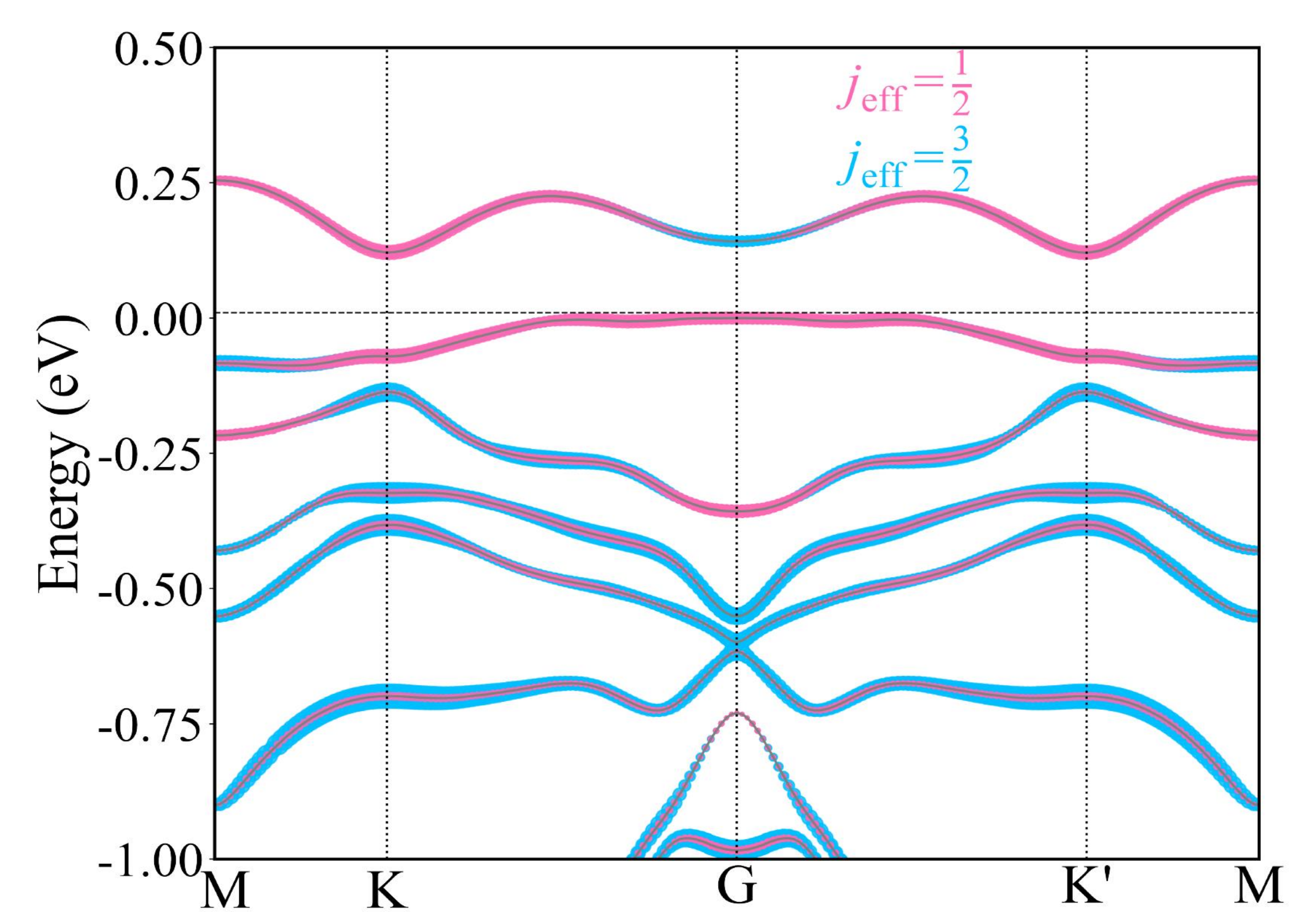
crystal field level diagram



bulk:  $j_{\text{eff}} = 1/2$  NM metallic state



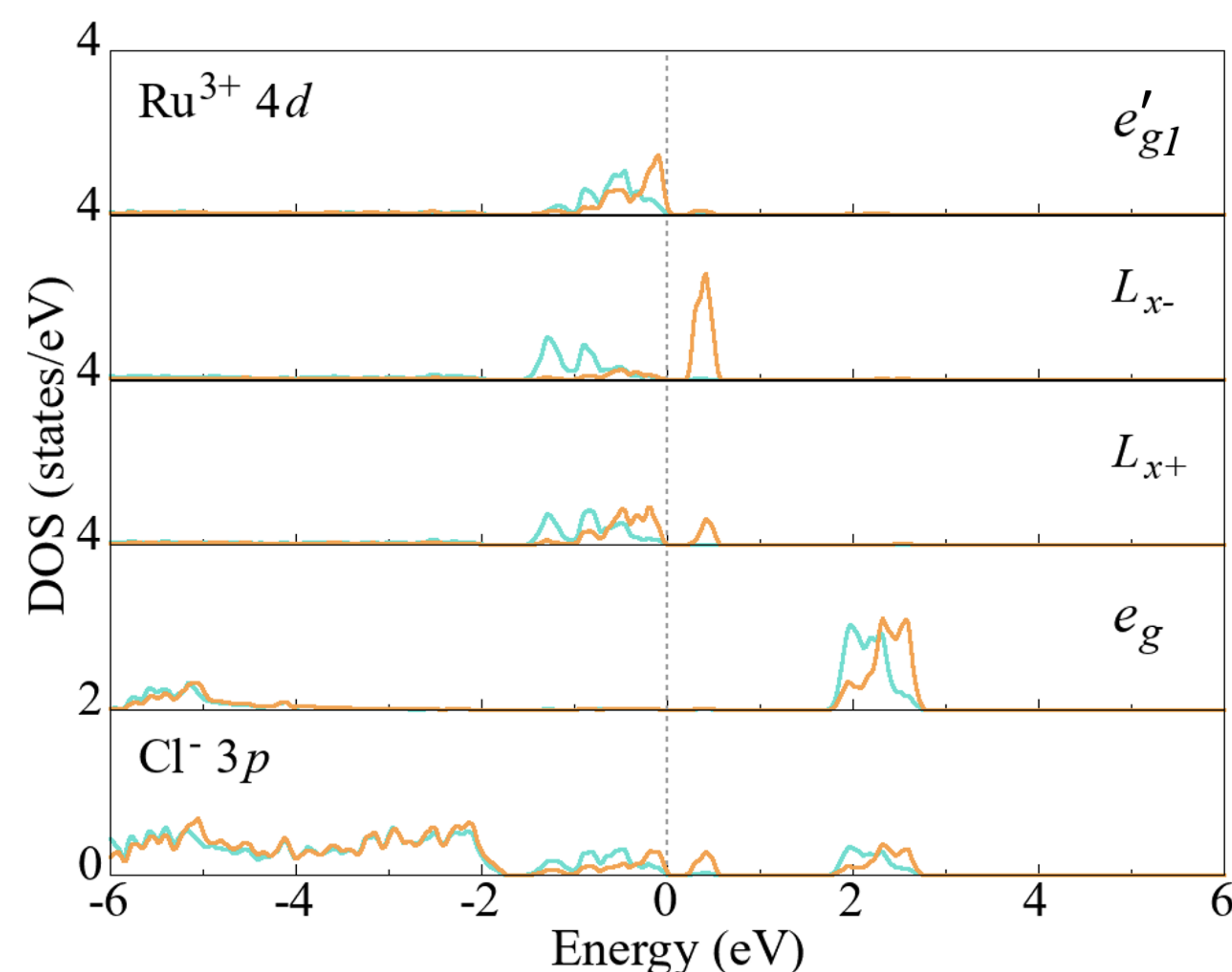
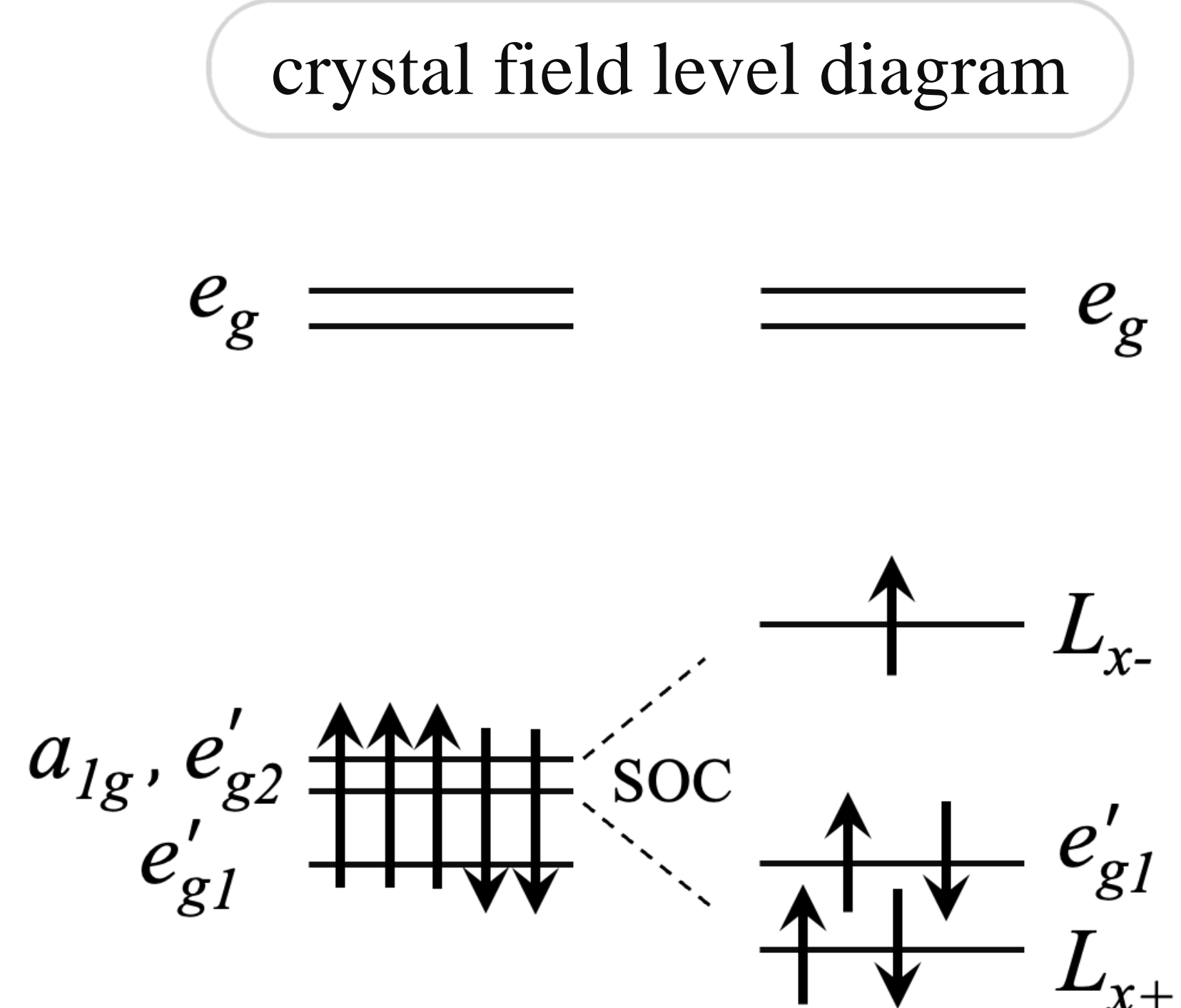
monolayer:  $j_{\text{eff}} = 1/2$  NM insulating state



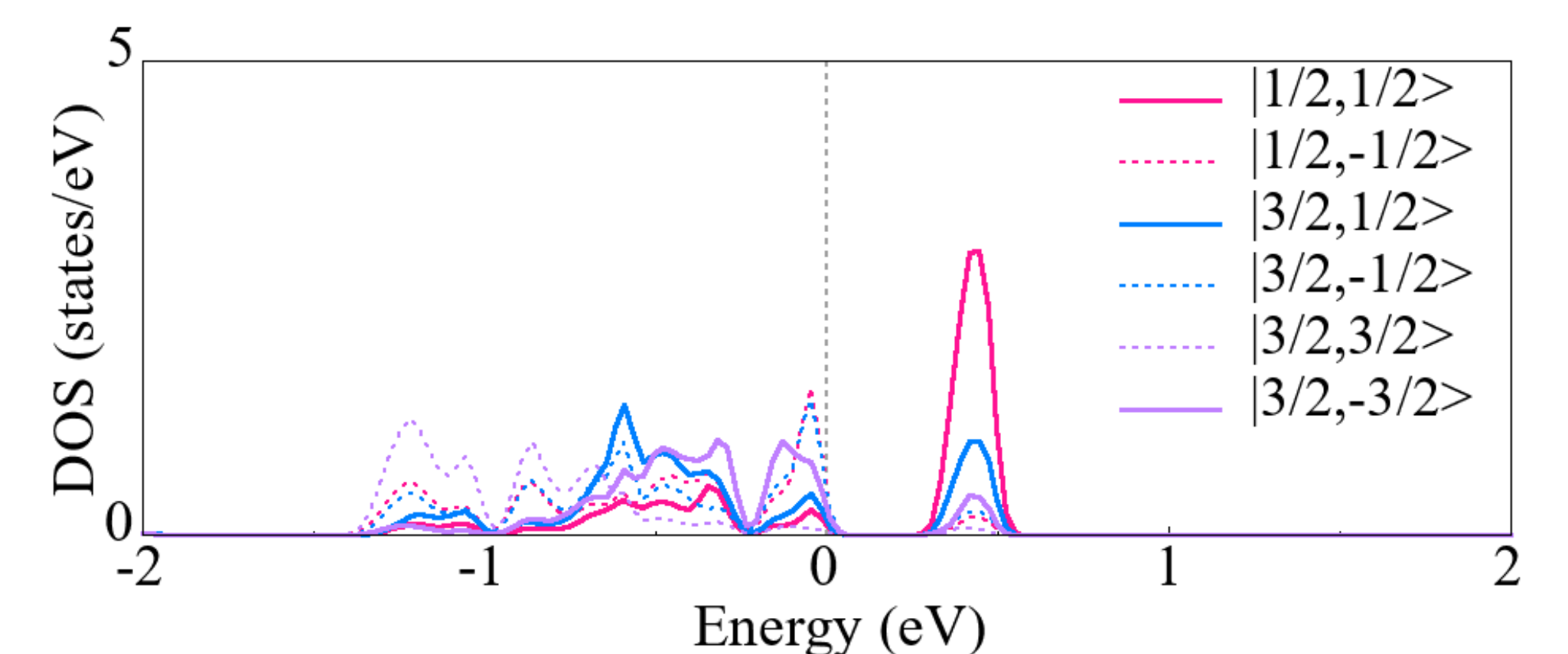
## $\text{RuCl}_3$

weak Ru 4d-Cl 3p hybridization & strong spin polarization  $\rightarrow$  **Hund exchange & trigonal splitting-dominant**

bulk & monolayer:  $S = 1/2$  and  $L_x = 1$  Mott-insulating state



project onto  $j_{\text{eff}} = 1/2$  basis



**$j_{\text{eff}} = 1/2$  is not suitable for  $\text{RuCl}_3$ !**

### Experiments:

- zigzag AFM insulator
- $g$  factors:  $g_{\text{ab}} > g_{\text{c}}$
- $M_{\text{in-plane}} \sim 1.2 \mu_{\text{B}}/\text{Ru}^{3+}$
- $\mu_{\text{eff}} = 2.0-2.4 \mu_{\text{B}}/\text{Ru}^{3+}$

### Our work:

- zigzag AFM insulator
- in-plane magnetic anisotropy energy =  $26.7 \text{ meV}/\text{Ru}^{3+}$
- $M_{\text{spin}} + M_{\text{orb}} = 0.70 + 0.47 = 1.17 \mu_{\text{B}}/\text{Ru}^{3+}$
- $\mu_{\text{eff}} = \sqrt{g_s^2 S(S+1) + g_l^2 L(L+1)} = 2.24 \mu_{\text{B}}/\text{Ru}^{3+}$